


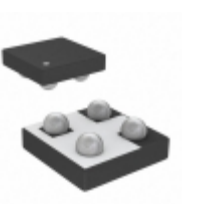

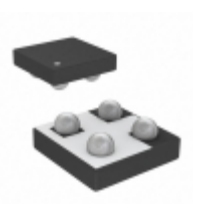
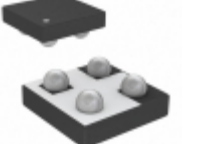


	<h2 style="color: red;">SI8405DB-T1-E1</h2>
 <p>Image may be representation. See specs for product details.</p>	Hersteller-Teilenummer: SI8405DB-T1-E1
	Hersteller / Marke: Electro-Films (EFI) / Vishay
	Teil der Beschreibung: MOSFET P-CH 12V 3.6A 2X2 4-MFP
	Datenblätter:  SI8405DB-T1-E1.pdf
	RoHs Status: Bleifrei / RoHS-konform
	Lagerzustand: New original, 3070 pcs Stock Available.
Liefern von: Hong Kong	
Versandweg: DHL/Fedex/TNT/UPS/EMS	

Spezifikationen

Teilenummer	SI8405DB-T1-E1
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET P-CH 12V 3.6A 2X2 4-MFP
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	3070 pcs Stock
detaillierte Beschreibung	P-Channel 12V 3.6A (Ta) 1.47W (Ta) Surface Mount 4-
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	4-XFBGA, CSPBGA
Supplier Device-Gehäuse	4-Microfoot
Verlustleistung (max)	1.47W (Ta)
Typ FET	P-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	12V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	3.6A (Ta)
Rds On (Max) @ Id, Vgs	55 mOhm @ 1A, 4.5V
VGS (th) (Max) @ Id	950mV @ 250µA
Gate Charge (Qg) (Max) @ Vgs	21nC @ 4.5V
Antriebsspannung (Max Rds On, Min Rds On)	1.8V, 4.5V
Vgs (Max)	±8V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	SI8405DB-T1-E1CT

SI8405DB-T1-E1 ist neu im Original, Suche SI8405DB-T1-E1 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI8405DB-T1-E1 Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage SI8405DB-T1-E1: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI8406DB-T2-E1 Vishay / Siliconix MOSFET N-CH 20V 16A MICROFOOT</p>	 <p>SI8405DB-T1-E1 Vishay / Siliconix MOSFET P-CH 12V 3.6A 2X2 4-MFP</p>	 <p>SI8405DB-T1 VISHAY SI8405DB-T1 VISHAY</p>	 <p>SI8405DB-T1-E3 Vishay / Siliconix MOSFET P-CH 12V 3.6A 2X2 4-MFP</p>
 <p>SI8405AB-B-IS1 Energy Micro (Silicon Labs) DGTLS ISO 2.5KV 4CH I2C 16SOIC</p>	 <p>SI8405DB-T1-E3 Electro-Films (EFI) / Vishay MOSFET P-CH 12V 3.6A 2X2 4-MFP</p>	 <p>SI8406DB-T2-E1 Electro-Films (EFI) / Vishay MOSFET N-CH 20V 16A MICROFOOT</p>	 <p>SI8405AB-B-IS1R Energy Micro (Silicon Labs) DGTLS ISO 2.5KV 4CH I2C 16SOIC</p>

heiße Teile

Mehr

SI8261BAC-C-IPR	SI8261BAC-C-IS	SI8261BAD-C-IS	SI8261BBC-C-IS	SI8261BBD-C-IS
SI8261BCC-C-IP	SI8261BCC-C-IS	SI8261BCD-C-IS	SI8388P-IU	SI8400AA-B-IS
SI8400AB-B-ISR	SI8401DB-T1	SI8401DB-T1-E1	SI8401DB-T1-E1	SI8401DB-T1-E3
SI8401DB-T1-E3	SI8402DB-T1	SI8402DB-T1-E1	SI8402DB-T1-E1	SI8402DB-T1-E1.
SI8402DB-T1-E3	SI8404DB-T1-E1	SI8404DB-T1-E1	SI8405DB	SI8405DB-T1
SI8405DB-T1-E1	SI8405DB-T1-E3	SI8405DB-T1-E3	SI8409DB-T1	SI8409DB-T1-E1
SI8409DB-T1-E1	SI8410AB	SI8410BB-D-ISR	SI8410BB-I-DS	SI8413DB-T1-E1
SI8413DB-T1-E1	SI8415DB-T1	SI8415DB-T1-E1	SI8415DB-T1-E1	SI8417DB-T2-E1
SI8417DB-T2-E1	SI8420BB	SI8420BB-D-IS	SI8421AB-D-ISR	SI8422AB-D-ISR
SI8422BD	SI8424DB-T1-E1	SI8424DB-T1-E1	SI8425DB-T1-E1	SI8425DB-T1-E1

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